

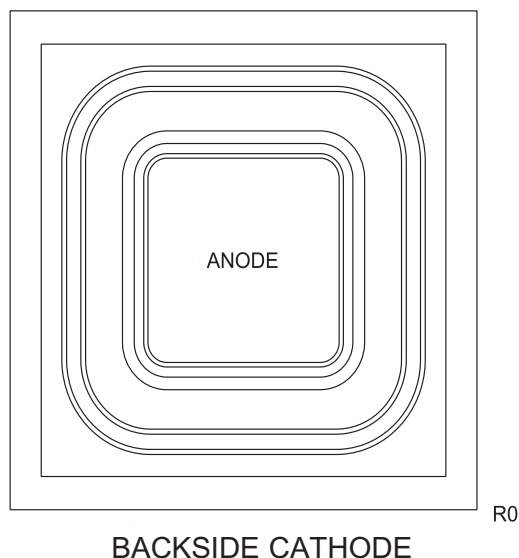
PROCESS CPD80V
Switching Diode
High Voltage Switching Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



GROSS DIE PER 5 INCH WAFER
64,704

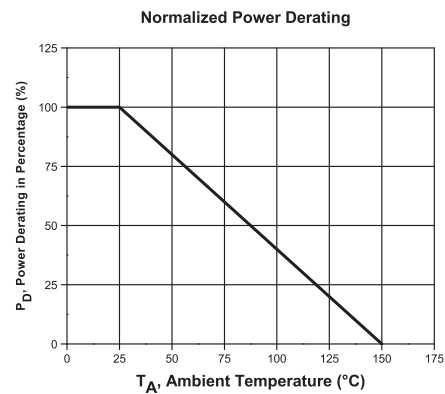
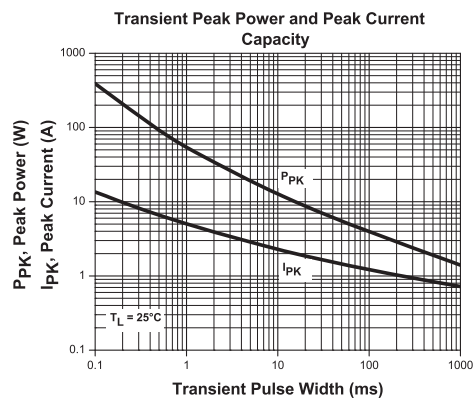
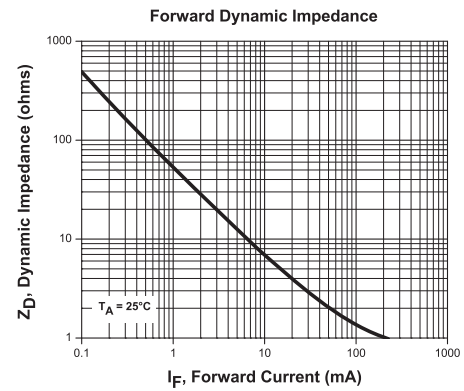
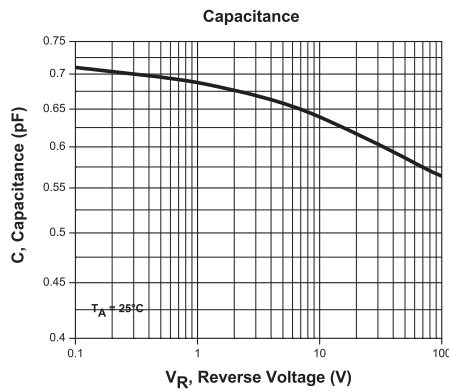
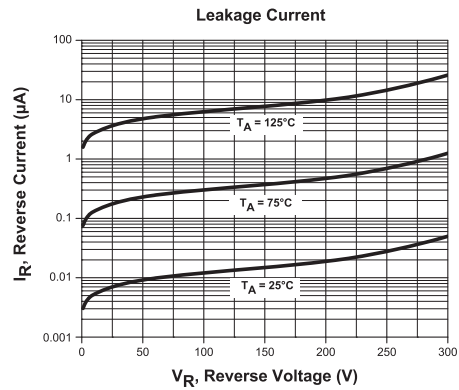
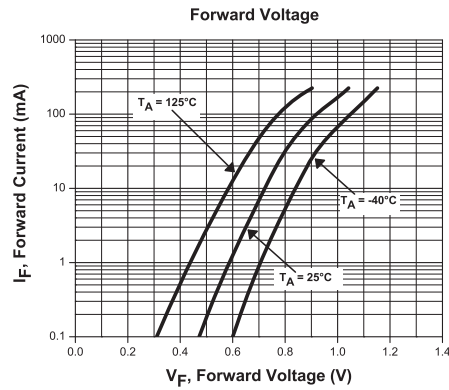
PRINCIPAL DEVICE TYPES

CMPD2003
CMPD2004
CMPD2005
1N3070
CMDD2004
CMSD2004
CMOD2004
CMXD2004
CMLD2004

R3 (22-March 2010)

PROCESS CPD80V

Typical Electrical Characteristics



R3 (22-March 2010)